

## SOT-227 Power Module Single Switch - Power MOSFET, 270 A



SOT-227

PRIMARY CHARACTERISTICS	
$V_{DSS}$	200 V
$R_{DS(on)}$	3.3 m $\Omega$
$I_D$	219 A at 90 °C
Type	Modules - MOSFET
Package	SOT-227

**FEATURES**

- $I_D = 287$  A,  $T_C = 25$  °C
- ThunderFET power MOSFET
- Reduced switching and conduction losses
- Maximum 175 °C junction temperature
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS  
COMPLIANT**
**APPLICATIONS**

- DC/DC conversions
- Motor drives switch
- DC/AC inverter
- Power supplies
  - Uninterruptible power supplies
  - AC/DC switchmode power supplies
  - Solar micro inverter

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
<b>MOSFET</b>				
Drain to source voltage	$V_{DSS}$		200	V
Continuous drain current, $V_{GS}$ at 10 V	$I_D$	$T_C = 25$ °C	287	A
		$T_C = 90$ °C	219	
Pulsed drain current	$I_{DM}^{(1)}$		680	
Power dissipation	$P_D$	$T_C = 25$ °C	937	W
Gate to source voltage	$V_{GS}$		$\pm 20$	V
Single pulse avalanche energy <sup>(2)</sup>	$E_{AS}$	$T_C = 25$ °C, $L = 0.1$ mH, $V_{GS} = 10$ V	650	mJ
Avalanche current	$I_{AS}$		180	A
<b>MODULE</b>				
Operating junction temperature range	$T_J$		-55 to +175	°C
Operating storage temperature range	$T_{Stg}$		-40 to +150	
Insulation voltage (RMS)	$V_{ISOL}$	Any terminal to case, $t = 1$ min	2500	V

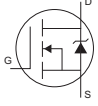
**Notes**

- (1) Limited at max. junction temperature  
 (2) Duty cycle  $\leq 1$  %



THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	$T_J$		-55	-	175	°C
Operating storage temperature range	$T_{Stg}$		-40	-	150	
Junction to case	MOSFET $R_{thJC}$		-	-	0.16	°C/W
Case to heatsink	Module $R_{thCS}$	Flat, greased surface	-	0.1	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf. in)
		Torque to heatsink	-	-	1.3 (11.5)	Nm (lbf. in)
Case style			SOT-227			

ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain to source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1.0\text{ mA}$	200	-	-	V
Breakdown voltage temperature coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	Reference to 25 °C, $I_D = 1.0\text{ mA}$	-	0.16	-	V/°C
Static drain to source on-resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 200\text{ A}$	-	3.3	4.7	mΩ
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1.0\text{ mA}$	1.8	3.16	4.3	V
Forward transconductance	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 100\text{ A}, V_{GS} = 10\text{ V}$	-	270	-	S
Drain to source leakage current	$I_{DSS}$	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	-	0.5	10	μA
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ °C}$	-	160	-	
Gate to source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	± 200	nA
Total gate charge	$Q_g$	$I_D = 120\text{ A}$ $V_{DS} = 100\text{ V}$ $V_{GS} = 10\text{ V}$	-	250	-	nC
Gate to source charge	$Q_{gs}$		-	68	-	
Gate to drain ("Miller") charge	$Q_{gd}$		-	70	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 100\text{ V}$ $I_D = 100\text{ A}$ $R_g = 1\text{ }\Omega$ $V_{GS} = 10\text{ V}$	-	76	-	ns
Rise time	$t_r$		-	212	-	
Turn-off delay time	$t_{d(off)}$		-	134	-	
Fall time	$t_f$		-	118	-	
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ $V_{DS} = 100\text{ V}$ $f = 1\text{ MHz}$	-	16.5	-	nF
Output capacitance	$C_{oss}$		-	1.0	-	
Reverse transfer capacitance	$C_{rss}$		-	0.8	-	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{DS} = V_{GS}, I_D = 1.0\text{ mA}$ (25 °C to 125 °C)	-	9.2	-	mV/°

SOURCE-DRAIN RATINGS AND CHARACTERISTICS ( $T_J = 25\text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Continuous source current (body diode)	$I_S$	MOSFET symbol showing the integral reverse p-n junction diode 	-	-	287	A
Pulsed source current (body diode)	$I_{SM}$		-	-	680	
Diode forward voltage	$V_{SD}$	$I_S = 200\text{ A}, V_{GS} = 0\text{ V}$	-	0.93	1.23	V
Reverse recovery time	$t_{rr}$	$T_J = 25\text{ °C}, I_F = I_S = 50\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$	-	210	-	ns
Reverse recovery charge	$Q_{rr}$		-	1646	-	nC
Reverse recovery current	$I_{RM}$		-	15.7	-	A

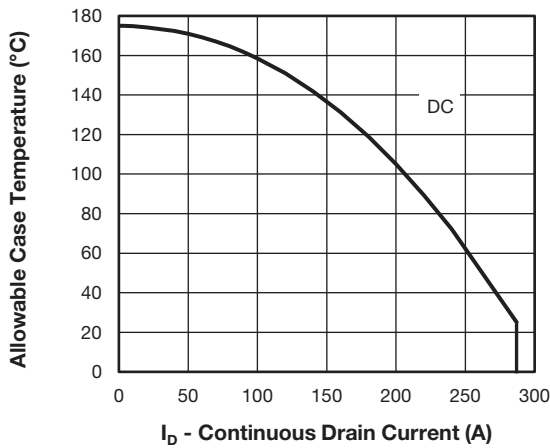


Fig. 1 - Maximum Continuous Drain Current vs. Case Temperature

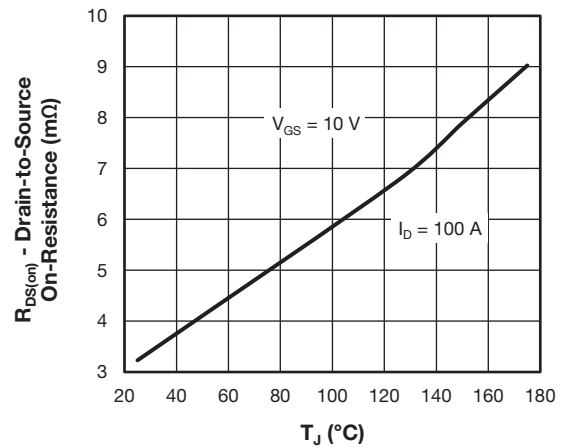


Fig. 4 - Typical Drain-to-Source On-Resistance vs. Temperature

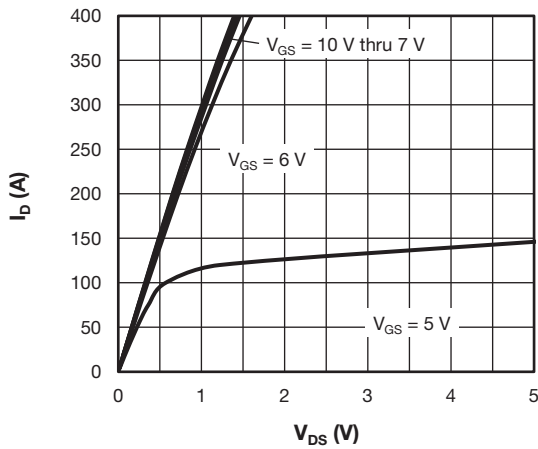


Fig. 2 - Typical Drain to Source Current Output Characteristics at  $T_J = 125^\circ\text{C}$

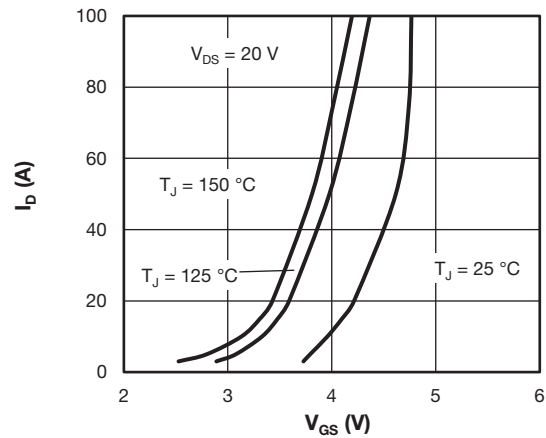


Fig. 5 - Typical Transfer Characteristics

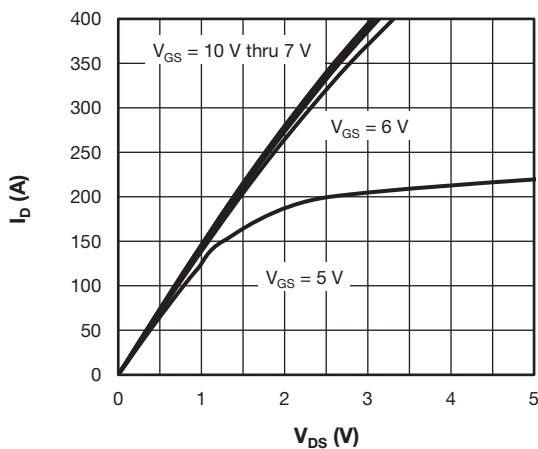


Fig. 3 - Typical Drain to Source Current Output Characteristics at  $T_J = 125^\circ\text{C}$

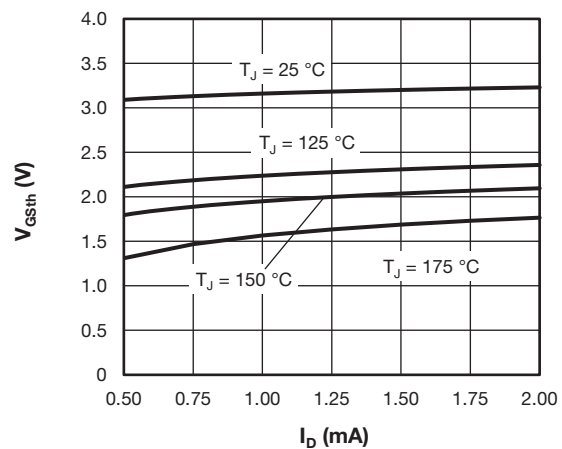


Fig. 6 - Typical Gate Threshold Voltage Characteristics

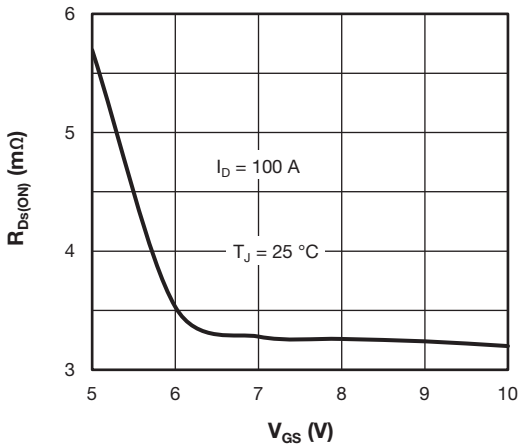


Fig. 7 - Typical Drain - State Resistance vs. Gate to Source Voltage

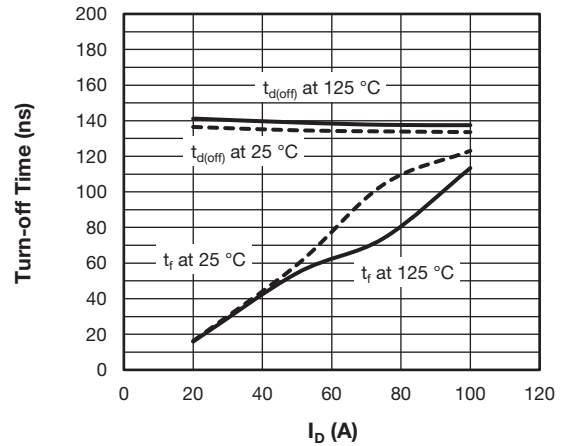


Fig. 10 - Typical Turn-Off Switching Time vs.  $I_D$ ,  $V_{DD} = 100\text{ V}$ ,  $R_g = 1.0\ \Omega$ ,  $V_{GS} = \pm 10\text{ V}$ ,  $L = 500\ \mu\text{H}$

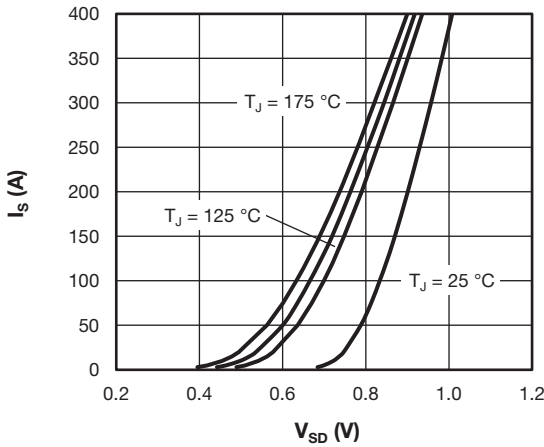


Fig. 8 - Typical Body Diode Source-to-Drain Current Characteristics

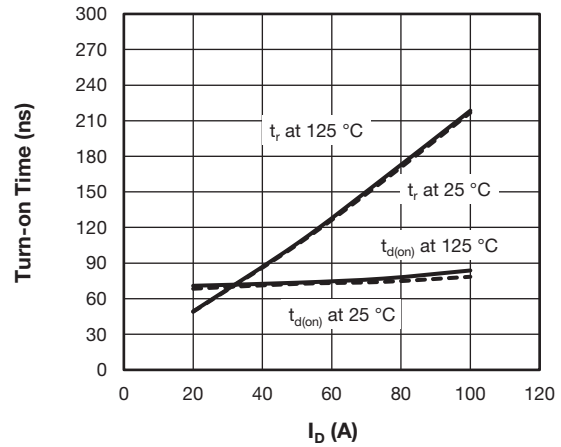


Fig. 11 - Typical Turn-On Switching Time vs.  $I_D$ ,  $V_{DD} = 100\text{ V}$ ,  $R_g = 1.0\ \Omega$ ,  $V_{GS} = \pm 10\text{ V}$ ,  $L = 500\ \mu\text{H}$

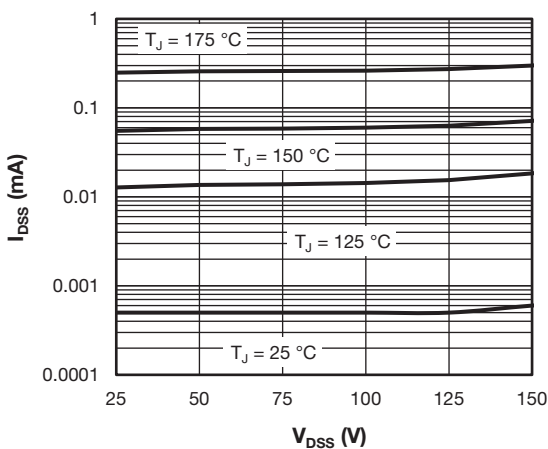


Fig. 9 - Typical Zero Gate Voltage Drain Current

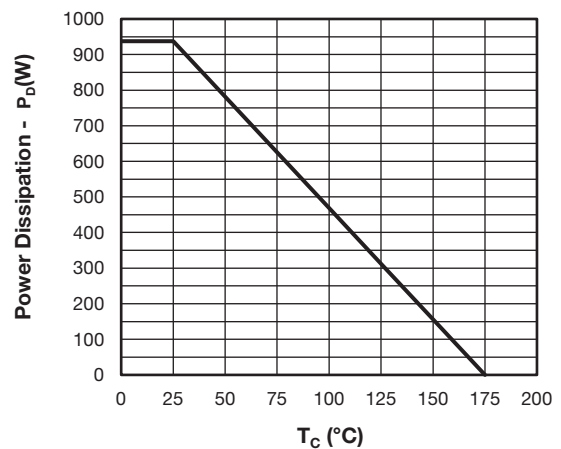


Fig. 12 - Power Dissipation Curve

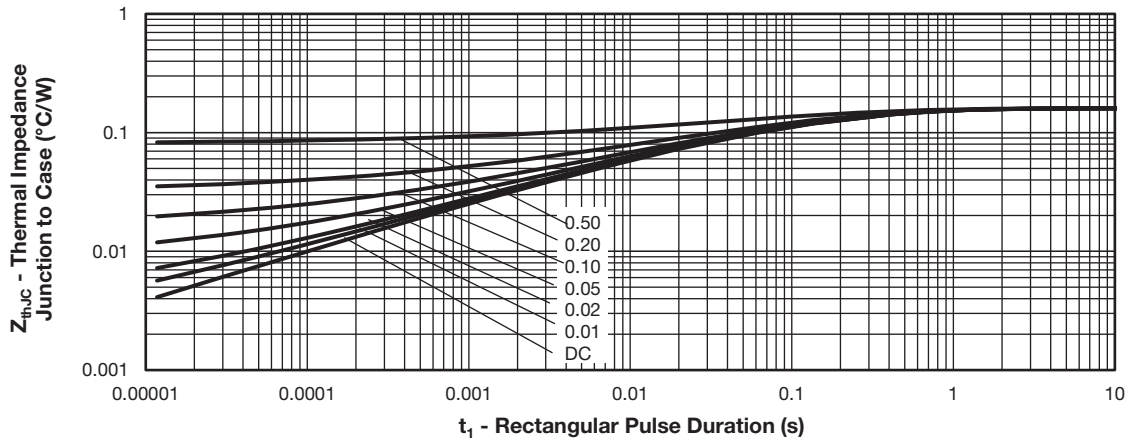


Fig. 13 - Maximum Thermal Impedance Junction-to-Case Characteristics

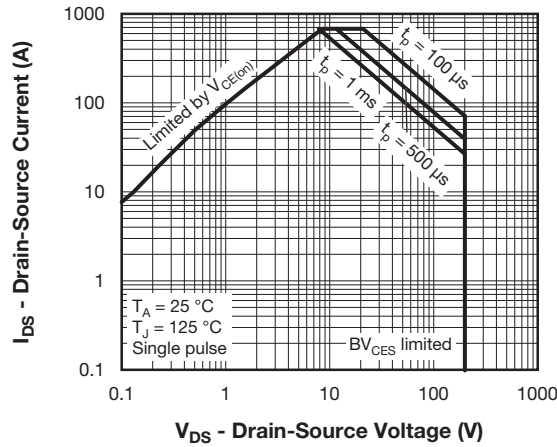


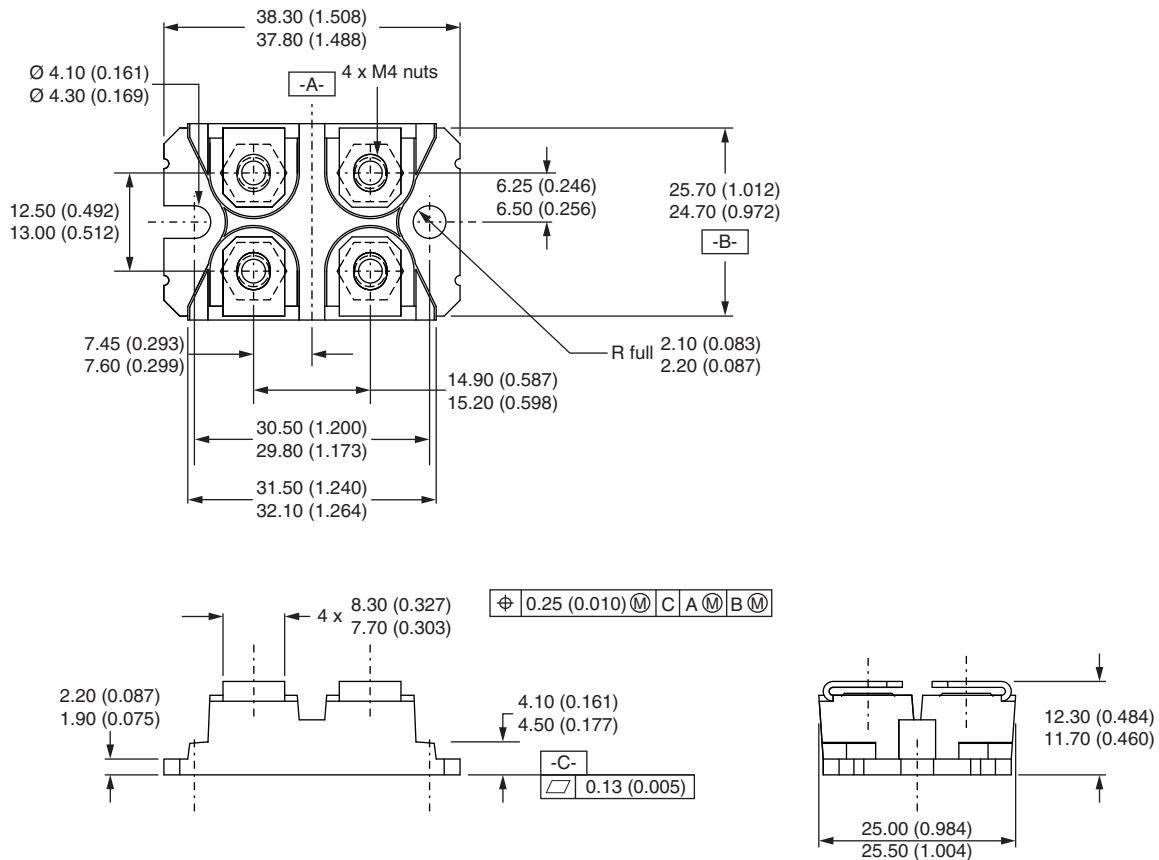
Fig. 14 - Safe Operating Area

**ORDERING INFORMATION TABLE**

Device code	<b>VS-</b>	<b>F</b>	<b>C</b>	<b>270</b>	<b>S</b>	<b>A</b>	<b>20</b>
	①	②	③	④	⑤	⑥	⑦

- 1** - Vishay Semiconductors product
- 2** - MOSFET module
- 3** - MOSFET die generation
- 4** - Current rating (270 = 270 A)
- 5** - Circuit configuration (S = single switch)
- 6** - Package indicator (SOT-227)
- 7** - Voltage rating (20 = 200 V)

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Single switch	S	

**DIMENSIONS** in millimeters




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